

## ABSTRACT OF THE DISCLOSURE

A test method for a semiconductor device in which a bonding pad thereof comprises a first interconnect layer and a second interconnect layer, the bonding pad  
5 comprising: a plurality of connection parts, provided within a plurality of slit-shaped trenches formed in an interlayer insulation film, respectively, and connecting the first interconnect layer and the second interconnect layer, the connection parts being disposed in one  
10 direction with a prescribed spacing, wherein the method comprising; contacting a test probe for testing the semiconductor device with the bonding pads so as to be in a direction parallel to a longitudinal direction of the connection part.